

Final

Course Code: 1930411

MLRS- R19



MARRI LAXMAN REDDY
INSTITUTE OF TECHNOLOGY AND MANAGEMENT
(AN AUTONOMOUS INSTITUTION)
(Approved by AICTE, New Delhi & Affiliated to JNTUH, Hyderabad)
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II B.Tech I Sem Regular End Examination, March 2021
ELECTRONIC DEVICES AND CIRCUITS
(ECE)

Time: 3 Hours.

Max. Marks: 70

Note: 1. Answer any FIVE questions.

2. Each question carries 14 marks and may have a, b as sub questions.

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| 1 | a) | Discuss switching characteristics of P-N junction diode? Explain load line? | 7M | C01 | BL |
| | b) | Define diffusion and transition capacitance? Explain about junction capacitance? | 7M | C01 | BL |
| 2 | a) | Sketch neat diagram of V-I characteristics of P-N junction diode for forward and reverse bias and explain? | 7M | C01 | BL |
| | b) | What is a step graded junction? Derive the expression for $C_T = \epsilon A/w$ | 7M | C01 | BL |
| 3 | a) | Discuss current components of BJT in detail. | 7M | C02 | BL |
| | b) | Explain early effect or Base width modulation. Define punch through. | 7M | C02 | BL |
| 4 | a) | Explain operation field effected transistor with neat diagram. | 7M | C02 | BL |
| | b) | Sketch drain and transfer characteristics of JFET and explain. | 7M | C03 | BL |
| 5 | a) | Sketch neat diagram of I/P & O/P of V-I characteristics of common Base configuration and explain. | 7M | C03 | BL |
| | b) | What are the advantages of JFET over BJT? | 7M | C03 | BL |
| 6 | a) | Why hybrid parameters are used for the analysis of BJT Amplifier and draw the h-parameter model for CE and CC configuration. | 7M | C04 | BL |
| | b) | Derive the expressions for current gain (A_I), voltage gain (A_V), Input Impedance (Z_i) and output Impedance (Z_o) using h-parameter model. | 7M | C04 | BL |
| 7 | a) | A CE amplifier is driven by a voltage source of internal resistance $R_S = 1K\Omega$ and load resistance is $R_L = 1.2K\Omega$. The h-parameters are $h_{ie} = 1K\Omega$, $h_{re} = 2 \times 10^{-4}$, $h_{fe} = 50$ and $h_{oe} = 25\mu A/V$. Determine A_I , A_V , Z_i and Z_o . | 7M | C04 | BL |
| | b) | Explain the small signal model of FET. | 7M | C05 | BL |
| 8 | a) | Derive expression for voltage gain (A_V), input impedance (Z_i) and output impedance (Z_o) of common source FET Amplifier. | 7M | C05 | BL |
| | b) | In CS Amplifier $R_D = 5K\Omega$, $R_G = 11M\Omega$, $\mu = 50$, and $r_d = 30K\Omega$. Find A_V , Z_i and Z_o . | 7M | C05 | BL |